

ZVNL120A-VB Datasheet

N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	200	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.8
Q_g (Max.) (nC)	4.8	
Q_{gs} (nC)	0.56	
Q_{gd} (nC)	1.3	
Configuration	Single	

FEATURES

- Low On-Resistance
- Secondary Breakdown Free
- Low Power/Voltage Driven
- Low Input and Output Leakage
- Excellent Thermal Stability



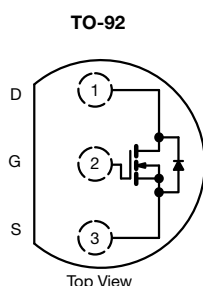
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- High-Voltage Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Transistors, etc.
- Telephone Mute Switches, Ringer Circuits
- Power Supply, Converters
- Motor Control

BENEFITS

- Low Offset Voltage
- Full-Voltage Operation
- Easily Driven Without Buffer
- Low Error Voltage
- No High-Temperature "Run-Away"



ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	200	V
Gate-Source Voltage			V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	0.6	A
		T _C = 70 °C		0.4	
Pulsed Drain Current ^a			I _{DM}	2.4	W/°C
Linear Derating Factor				0.33	
Linear Derating Factor (PCB Mount)				0.020	
Single Pulse Avalanche Energy			E _{AS}	54	mJ
Repetitive Avalanche Current			I _{AR}	1.0	A
Repetitive Avalanche Energy			E _{AR}	2.2	mJ
Maximum Power Dissipation	T _A = 25 °C		P _D	1.6	W
Maximum Power Dissipation (PCB Mount)	T _A = 75 °C			1.2	
Peak Diode Recovery dV/dt			dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			260 ^d	

SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Limits			
			Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 100 μA	200			V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.8	1.65	2	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 192 V, V _{GS} = 0 V			1	μA
		V _{DS} = 192 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 10 V, V _{GS} = 10 V	0.8			A
		V _{DS} = 10 V, V _{GS} = 4.5 V	0.5			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.6 A		0.8		Ω
		V _{GS} = 4.5 V, I _D = 0.5 A		1.0		
		V _{GS} = 2.5 V, I _D = 0.3 A		1.6		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 0.6 A		1.6		S
Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 0.6 A		0.8	1.2	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = 192 V, V _{GS} = 10 V, I _D = 0.5 A		4.87	8	nC
Gate-Source Charge	Q _{gs}			0.56		
Gate-Drain Charge	Q _{gd}			1.53		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 60 V, R _L = 200 Ω I _D ≅ 0.3 A, V _{GEN} = 10 V, R _g = 25 Ω		5	10	ns
Rise Time	t _r			12	20	
Turn-Off Delay Time	t _{d(off)}			35	60	
Fall Time	t _f			16	25	

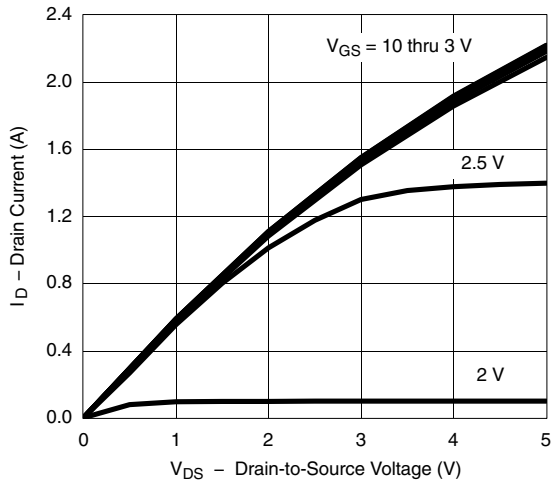
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

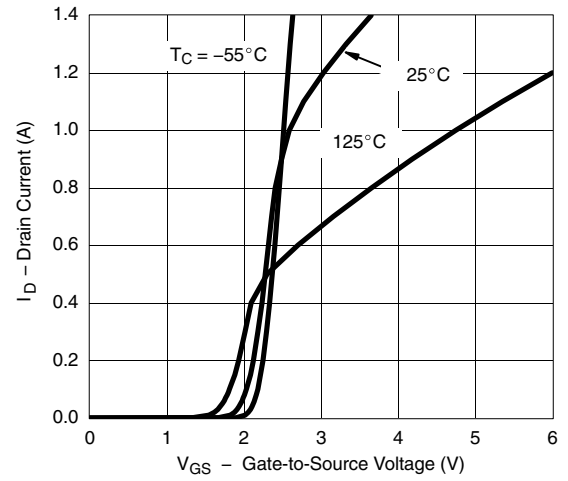
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

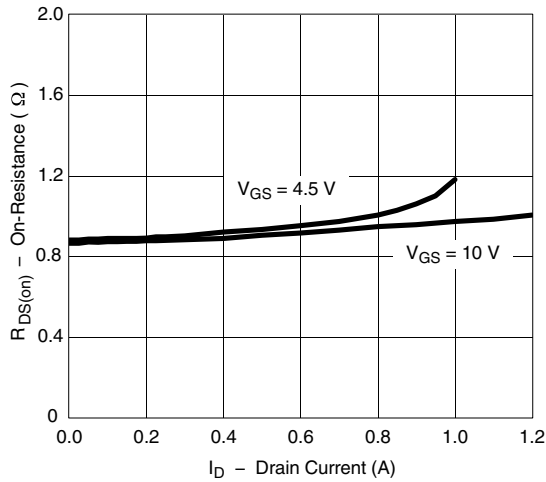
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



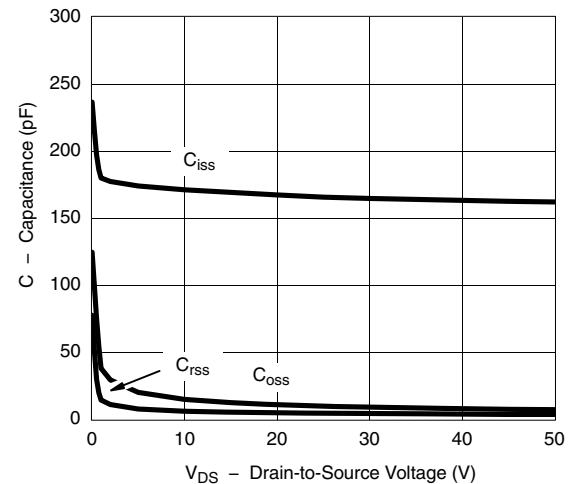
Output Characteristics



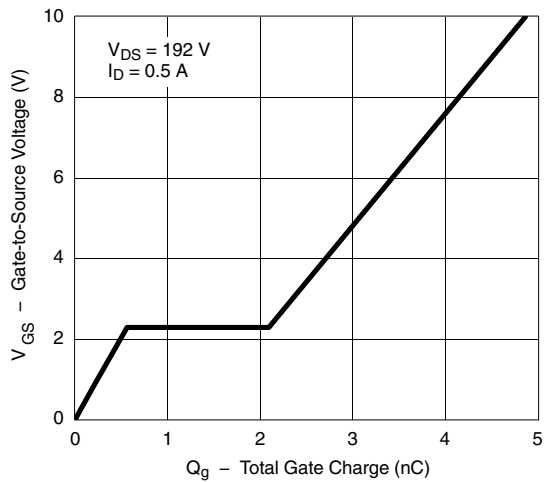
Transfer Characteristics



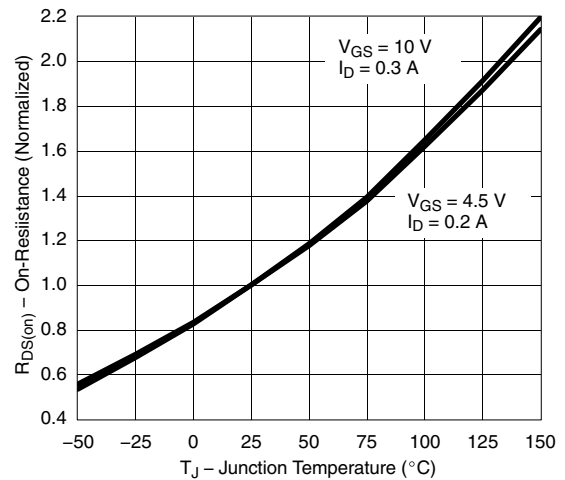
On-Resistance vs. Drain Current



Capacitance

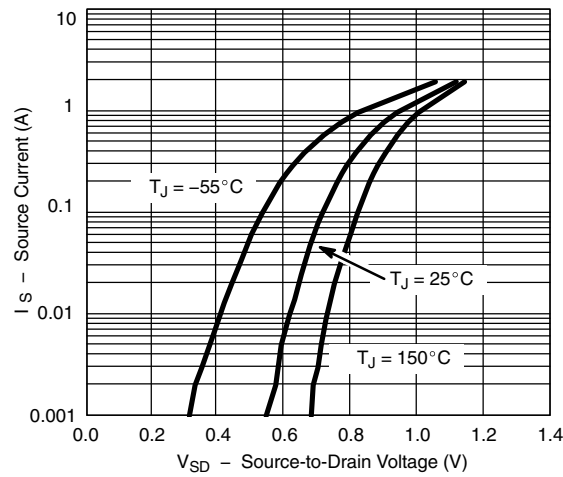


Gate Charge

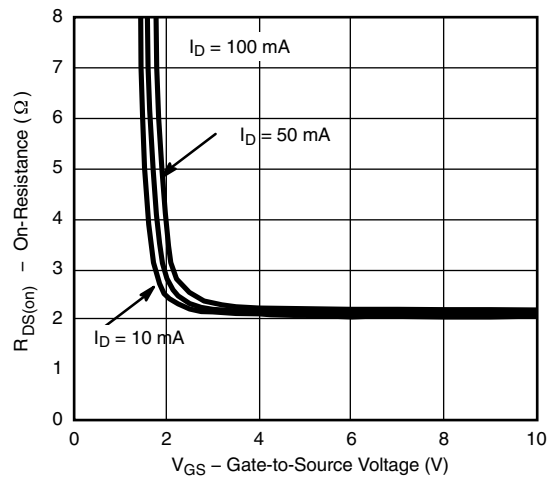


On-Resistance vs. Junction Temperature

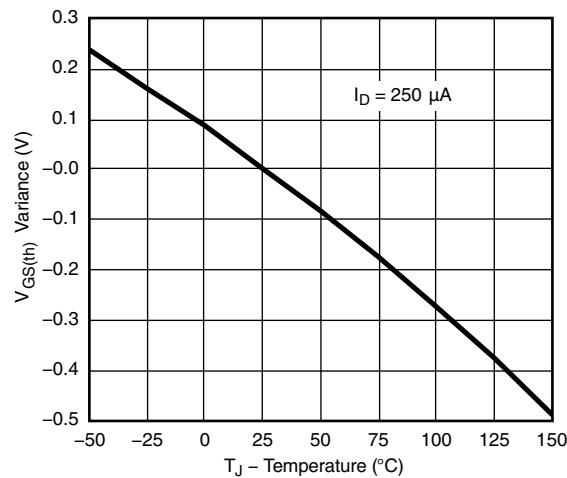
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Source-Drain Diode Forward Voltage

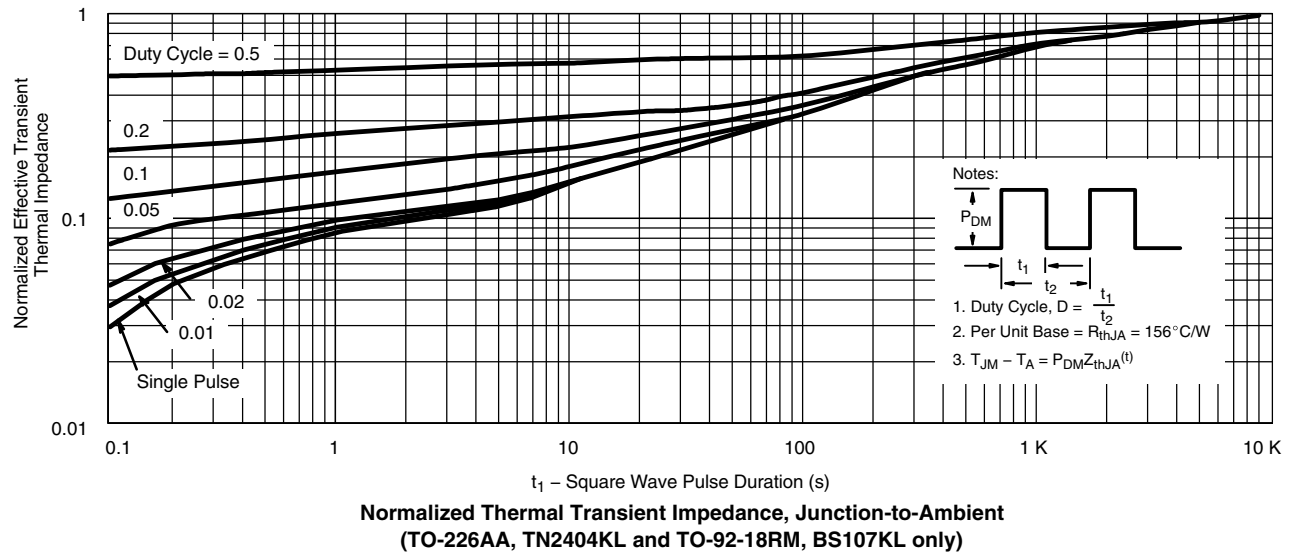
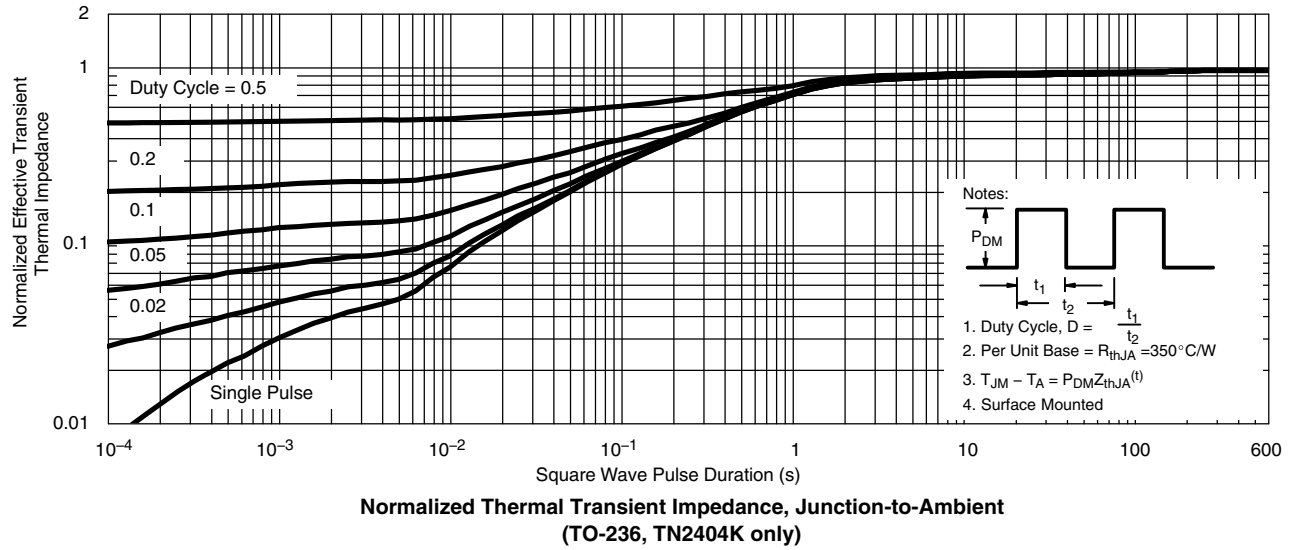


On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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